

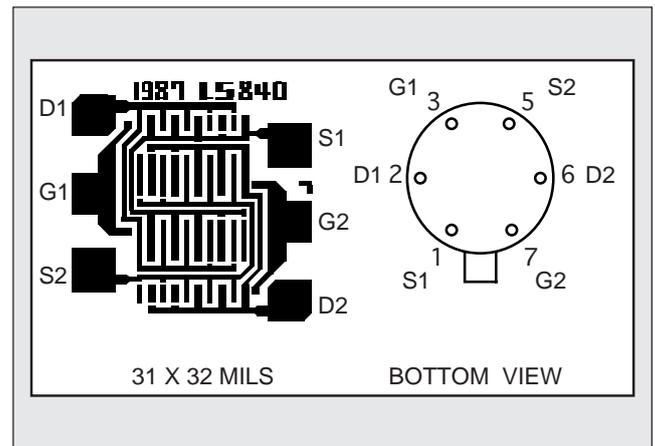
# LINEAR SYSTEMS

Linear Integrated Systems

## LS840 LS841 LS842

LOW NOISE LOW DRIFT  
LOW CAPACITANCE  
MONOLITHIC DUAL N-CHANNEL JFET

FEATURES		
LOW NOISE	$e_n = 8nV/\sqrt{Hz}$ TYP.	
LOW LEAKAGE	$I_G = 10pA$ TYP.	
LOW DRIFT	$ \Delta V_{GS1-2}/\Delta T  = 5\mu V/^\circ C$ max.	
LOW OFFSET VOLTAGE	$ V_{GS1-2}  = 2mV$ TYP.	
ABSOLUTE MAXIMUM RATINGS NOTE 1 @ 25°C (unless otherwise noted)		
Maximum Temperatures		
Storage Temperature	-65° to +150°C	
Operating Junction Temperature	+150°C	
Maximum Voltage and Current for Each Transistor NOTE 1		
-V <sub>GSS</sub>	Gate Voltage to Drain or Source	60V
-V <sub>DSO</sub>	Drain to Source Voltage	60V
-I <sub>G(f)</sub>	Gate Forward Current	50mA
Maximum Power Dissipation		
Device Dissipation @ Free Air - Total		400mW @ +125°C



### ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

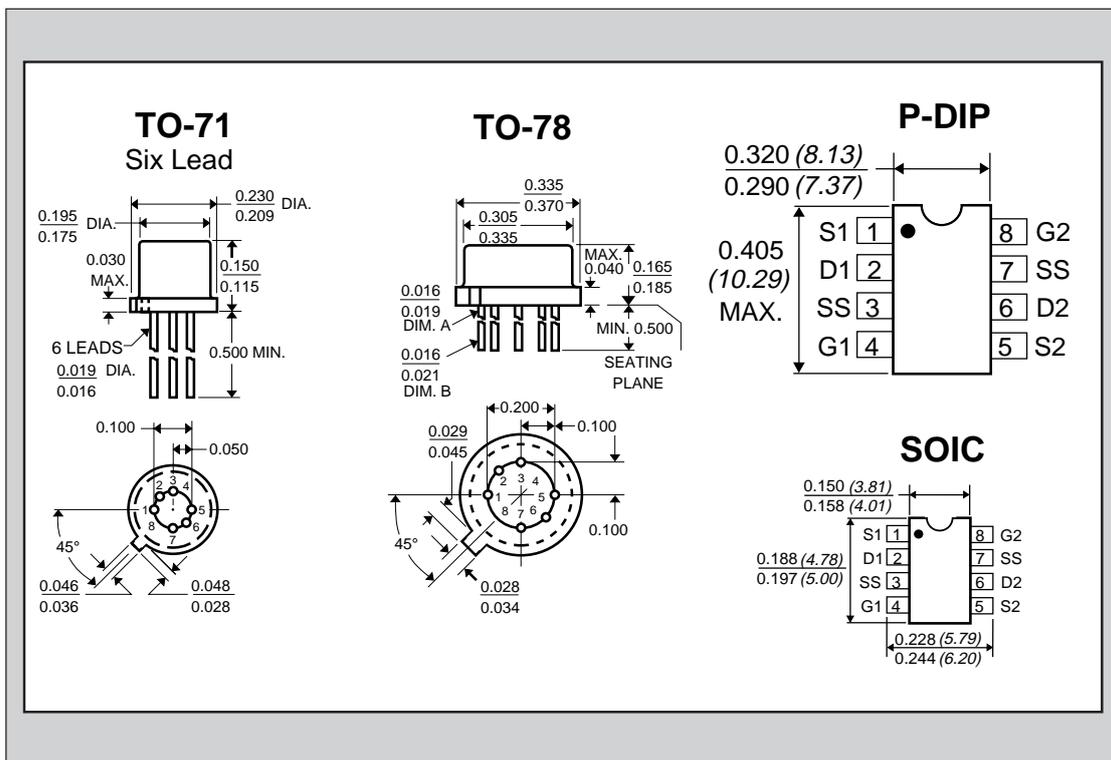
SYMBOL	CHARACTERISTICS	LS840	LS841	LS842	UNITS	CONDITIONS
$ \Delta V_{GS1-2}/\Delta T $ max.	Drift vs. Temperature	5	10	40	$\mu V/^\circ C$	$V_{DG} = 20V$ $T_A = -55^\circ C$ to $+125^\circ C$ $I_D = 200\mu A$
$ V_{GS1-2} $ max.	Offset Voltage	5	10	25	mV	$V_{DG} = 20V$ $I_D = 200\mu A$

SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
BV <sub>GSS</sub>	Breakdown Voltage	60	--	--	V	$V_{DS} = 0$ $I_D = 1nA$
BV <sub>GGO</sub>	Gate-to-Gate Breakdown	60	--	--	V	$I_G = 1nA$ $I_D = 0$ $I_S = 0$
TRANSCONDUCTANCE						
Y <sub>fss</sub>	Full Conduction	1000		4000	$\mu mho$	$V_{DG} = 20V$ $V_{GS} = 0$ $f = 1kHz$
Y <sub>fs</sub>	Typical Conduction	500		1000	$\mu mho$	$V_{DG} = 20V$ $I_D = 200\mu A$
$ Y_{fs1-2}/Y_{fs} $	Mismatch	--	0.6	3	%	
DRAIN CURRENT						
I <sub>DSS</sub>	Full Conduction	0.5	2	5	mA	$V_{DG} = 20V$ $V_{GS} = 0$
$ I_{DSS1-2}/I_{DSS} $	Mismatch at Full Conduction	--	1	5	%	
GATE VOLTAGE						
V <sub>GS(off)</sub> or V <sub>P</sub>	Pinchoff Voltage	1	2	4.5	V	$V_{DS} = 20V$ $I_D = 1nA$
V <sub>GS</sub>	Operating Range	0.5	--	4	V	$V_{DS} = 20V$ $I_D = 200\mu A$
GATE CURRENT						
-I <sub>G</sub>	Operating	--	10	50	pA	$V_{DG} = 20V$ $I_D = 200\mu A$
-I <sub>G</sub>	High Temperature	--	--	50	nA	$V_{DG} = 20V$ $I_D = 200\mu A$ $T_A = +125^\circ C$
-I <sub>G</sub>	Reduced VDG	--	5	--	pA	$V_{DG} = 10V$ $I_D = 200\mu A$
-I <sub>GSS</sub>	At Full Conduction	--	--	100	pA	$V_{DG} = 20V$ $V_{DS} = 0$

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SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
	<b>OUTPUT CONDUCTANCE</b>					
$Y_{OSS}$	Full Conduction	--	--	10	$\mu\text{mho}$	$V_{DG} = 20\text{V}$ $V_{GS} = 0$
$Y_{OS}$	Operating	--	0.1	1	$\mu\text{mho}$	$V_{DG} = 20\text{V}$ $I_D = 200\mu\text{A}$
$ Y_{OS1-2} $	Differential	--	0.01	0.1	$\mu\text{mho}$	
	<b>COMMON MODE REJECTION</b>					
CMR	$-20 \log  \Delta V_{GS1-2} / \Delta V_{DS} $	--	100	--	dB	$\Delta V_{DS} = 10 \text{ to } 20\text{V}$ $I_D = 200\mu\text{A}$
CMR		--	75	--	dB	$\Delta V_{DS} = 5 \text{ to } 10\text{V}$ $I_D = 200\mu\text{A}$
	<b>NOISE</b>					
NF	Figure	--	--	0.5	dB	$V_{DS} = 20\text{V}$ $V_{GS} = 0$ $R_G = 10\text{M}\Omega$ $f = 100\text{Hz}$ $\text{NBW} = 6\text{Hz}$
$e_n$	Voltage	--	--	10	$\text{nV}/\sqrt{\text{Hz}}$	$V_{DS} = 20\text{V}$ $I_D = 200\mu\text{A}$ $f = 1\text{KHz}$ $\text{NBW} = 1\text{Hz}$
$e_n$	Voltage	--	--	15	$\text{nV}/\sqrt{\text{Hz}}$	$V_{DS} = 20\text{V}$ $I_D = 200\mu\text{A}$ $f = 10\text{Hz}$ $\text{NBW} = 1\text{Hz}$
	<b>CAPACITANCE</b>					
$C_{ISS}$	Input	--	4	10	pF	$V_{DS} = 20\text{V}$ $I_D = 200\mu\text{A}$
$C_{RSS}$	Reverse Transfer	--	1.2	5	pF	
$C_{DD}$	Drain-to-Drain	--	0.1	--	pF	$V_{DG} = 20\text{V}$ $I_D = 200\mu\text{A}$



**NOTES:**

1. These ratings are limiting values above which the serviceability of any semiconductor may be impaired.